EAST Search History

EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	1146	remov$3 near3 (sige or germanium) near5 layer	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/07 16:15
S2	658	S1 and "438".clas.	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/07 16:15
S3	0	S2 and htdrogen peroxide	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/07 16:15
S4	126	S2 and hydrogen peroxide	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/07 16:15
S5	437	S2 and wafer	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/07 16:17
S6	93	S5 and peroxide	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/07 16:18
S7	9	S5 and diaphragm	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/07 16:22
S8	15	S1 and diaphragm	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/07 16:25
S9	6	S8 not S7	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/07 16:25
S10	4	("4888300" | "6100132").PN. OR ("7019364").URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/12/07 16:28
S11	93	flat near4 diaphragm near4 sensor	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/07 16:30
S12	567	dry etch$3 with (germanium or sige or ge)	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/07 16:57
S13	210	remov$3 with dry etch $3 with (germanium or sige or ge)	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/07 16:59
S14	2138	remov$3 with etch$3 with (germanium or sige or ge)	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/07 17:04

S15	1156	S14 and "438".clas.	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/07 17:05
S16	37	S15 and mem	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/07 17:05
S17	37	S15 and (mem or mems)	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/07 17:05
S18	131	(si or silicon) near4 substrate and flat diaphragm	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/07 17:12
S19	6	S18 and (germanium or sige or ge)	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/07 17:12
S20	64	(si or silicon) near4 substrate and flat sensor	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/07 17:18
S21	19	S20 and ("438".clas. or "257".clas.)	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/07 17:19
S22	1	("5291781").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2008/12/07 17:20
S23	18	("4471647" | "4501144" | "4542650" | "5050429").PN. OR ("5291781").URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2008/12/07 17:21
S24	1360	flat diaphragm	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/07 17:26
S25	1	S24 near4 germanium	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/07 17:26
S26	1009	257/417.ccls.	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/08 08:52
S27	732	diaphragm and sensor and germanium	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/08 08:52
S28	18	S26 and S27	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/08 08:52
S29	44	diaphragm same sensor same germanium	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/08 09:02
S30	10	diaphragm same sensor same germanium same substrate	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/08 09:25

S31	4537	sige layer	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/08 09:54
S32	1218	sige layer near3 substrate	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2008/12/08 09:54
S33	2202	(sensor or transducer). ti,ab. and ((germanium or $2ge) near5 diaphragm)	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2009/07/06 09:03
S34	694	S33 and substrate	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2009/07/06 09:04
S35	369	S33 and ((silicon or soi) near5 substrate)	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2009/07/06 09:04
S36	19	(sensor or transducer). ti,ab. and ((germanium or sige) near5 diaphragm)	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2009/07/06 09:05
S37	38302	438/50,53,460-465,690-757.ccls. or 257/415-419.ccls.	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2010/03/12 14:18
S38	492	etch$3 stop near5 (ge or sige or germanium)	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2010/03/12 14:19
S39	3182860	substrate or wafer	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2010/03/12 14:20
S40	172	S38 with S39	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2010/03/12 14:20
S41	5051	(remov$3 or etch$4) near3 (ge or sige or germanium)	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2010/03/12 14:20
S42	79	("4372803" | "4463336" | "4601779" | "4721938" | "4784721" | "4851080" | "4889590" | "4978421" | "5013681" | "5068203").PN. OR ("5413679").URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2010/03/12 15:33
S43	74	("4601779" | "4735679" | "4962051" | "4983251" | "5013681" | "5034343" | "5234535").PN. OR ("5310451").URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2010/03/12 15:42

S44	281396	diaphragm	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2010/03/12 16:25
S45	134	S41 and S44	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2010/03/12 16:25
S46	116	S45 not S40	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2010/03/12 16:25
S47	66	S38 and S44	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2010/03/12 16:34
S48	7	S47 not (S45 or S40)	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2010/03/12 16:35
S49	388	(438/465).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/07/27 13:56
S50	41573	etch near2 stop$4	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2010/07/27 13:58
S51	17	S49 and S50	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2010/07/27 13:58
S52	806	(sige or ge or germanium or group IV $1 or group "4") with (etch near2 stop$4)	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2010/07/28 09:53
S53	116273	(dic$3 or cut$4) near4 (wafer or substrate)	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2010/07/28 09:54
S54	151	S52 and S53	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2010/07/28 09:54
S55	1	("5,882,987").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/07/28 09:56
S56	10100	((dic$3) near4 (wafer or substrate)).ti,ab.	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2010/07/28 10:05
S57	0	S52 and S56	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2010/07/28 10:05
S58	37323	(dic$3) near4 (wafer or substrate)	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2010/07/28 10:05
S59	77	S52 and S58	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2010/07/28 10:05

S60	7894	(singulat$3) near4 (wafer or substrate)	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2010/07/28 10:08
S61	4	S52 and S60	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2010/07/28 10:09
S62	1	("7060531").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/07/29 10:53
S63	5	("5268065" | "5275958" | "5972781" | "6020217" | "6221751").PN. OR ("7060531").URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2010/07/29 10:53
S64	810	(sige or ge or germanium or group IV $1 or group "4") with (etch near2 stop$4)	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2010/07/29 11:05
S65	16	plasma near2 etch$3 with (S64)	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2010/07/29 11:05
S66	143331	plasma near2 etch$3 or rie	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2010/07/29 11:12
S67	33086	(dic$3 or singulat$3) near4 wafer	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2010/07/29 11:17
S69	47539	etch$3 near2 stop	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2010/07/29 11:30
S70	147	S66 with S69 and S67	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2010/07/29 11:30
S71	0	(10/274403).APP.	USPAT; USOCR	ADJ	ON	2010/07/29 11:38
S72	11	("20040067446" | "20070052322" | "4451349" | "5201987" | "5888882" | "5891354" | "6475881" | "6475881" | "6551849" | "6650387" | "6689950" | "6689950" | "6793389").PN.	US-PGPUB; USPAT	ADJ	ON	2010/07/29 11:40
S73	2	"20040009649"	US-PGPUB; USPAT	ADJ	ON	2010/07/29 12:24
S74	76164	dic$3 and thin$4	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2010/08/02 10:36

S75	32013	S74 and wafer	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2010/08/02 10:36
S76	9816	S75 and ("438".clas. or "324".clAs.)	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2010/08/02 10:36
S77	1604196	(germanium or sige or ge)	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2010/08/02 10:37
S78	1703	S76 and S77	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2010/08/02 10:37
S79	10890	(etch$3 or remov$3 or polish$ or thin$4 or grind$3) near4 S77	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2010/08/02 10:37
S80	137	S76 and S79	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2010/08/02 10:38
S81	4857	(etch$3 or remov$3 or polish$ or thin$4 or grind$3) near4 (layer or film) with (dic$3 or separat$3) with wafer	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2010/08/02 10:43
S82	781	S76 and S81	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2010/08/02 10:43
S83	767	S82 not S80	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2010/08/02 10:43
S84	2048	S81 and "438".clas.	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2010/08/02 10:46
S85	770	S81 and "438".clas. and S74 and S75	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2010/08/02 10:47
S86	756	S85 not S80	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2010/08/02 10:47
S87	52	(etch$3 or remov$3 or polish$ or thin$4 or grind$3) near4 (etch stop) with (dic$3 or separat$3) with (wafer or chip or ic or die)	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2010/08/02 10:56

S88	53	("3786307" | "3845615" | "4112333" | "4229736" | "4233602" | "4359729" | "4368467" | "4368523" | "4429305" | "4448491" | "4491391" | "4499459" | "4586039").PN. OR ("4808983").URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2010/08/02 11:03
S89	71	("3924323" | "4224101" | "5196378" | "5362681" | "5369060" | "5426072" | "5457072" | "5547906" | "5552345" | "5597766").PN. OR ("5904546").URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2010/08/02 11:13
S90	82	((ge or sige or germanium) with etch $3 stop) and ((dic$3 near2 wafer) or (separat$3 near2 (IC or die or chip or component)))	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2010/08/11 09:13
S91	35	S90 not leedy.inv.	US-PGPUB; USPAT; JPO; DERWENT	ADJ	ON	2010/08/11 09:15

EAST Search History (Interference)

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